

2SK3149

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

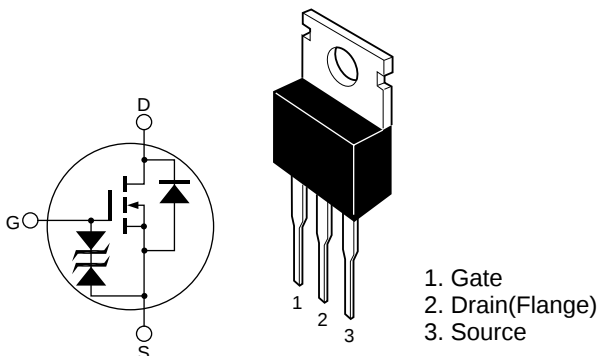
ADE-208-749A (Z)
2nd. Edition
February 1999

Features

- Low on-resistance
 $R_{DS} = 45 \text{ m}\Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline

TO-220AB



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	20	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	60	A
Body-drain diode reverse drain current	I_{DR}	20	A
Avalanche current	I_{AP} ^{Note3}	20	A
Avalanche energy	E_{AR} ^{Note3}	40	mJ
Channel dissipation	P_{ch} ^{Note2}	50	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$
3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

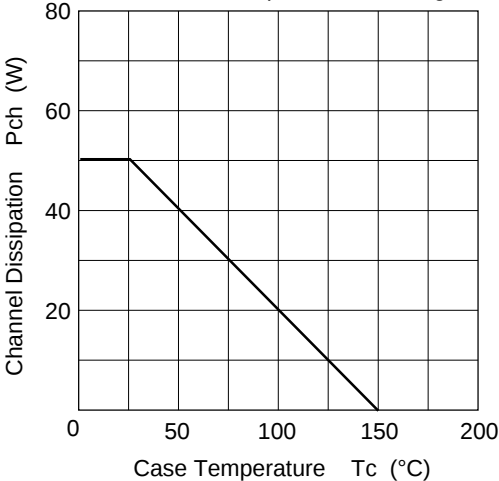
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	45	60	$m\Omega$	$I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	65	85	$m\Omega$	$I_D = 10 \text{ A}$, $V_{GS} = 4 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	8.5	15	—	S	$I_D = 10 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	900	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	400	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	210	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$
Rise time	t_r	—	120	—	ns	$R_L = 3 \Omega$
Turn-off delay time	$t_{d(off)}$	—	200	—	ns	
Fall time	t_f	—	150	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 20 \text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	90	—	ns	$I_F = 20 \text{ A}$, $V_{GS} = 0$ $diF/dt = 50 \text{ A}/\mu s$

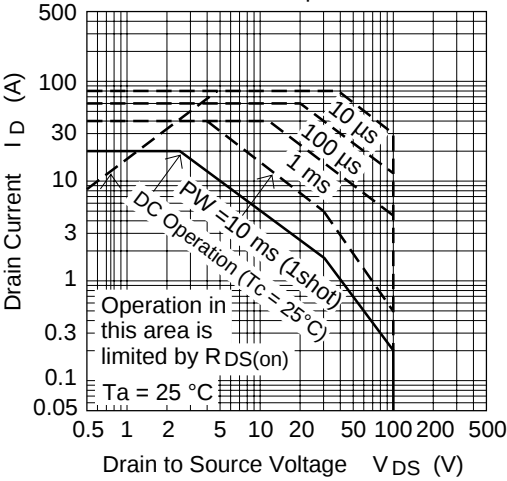
Note: 4. Pulse test

Main Characteristics

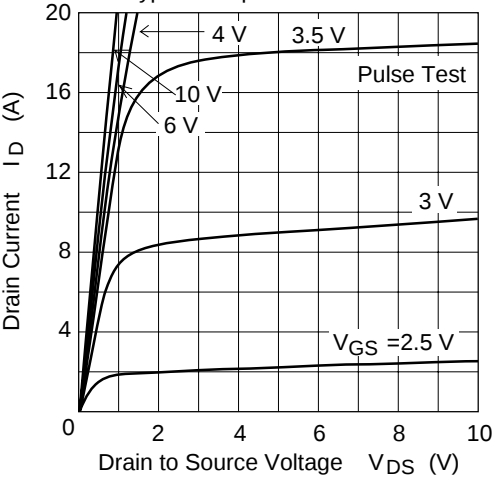
Power vs. Temperature Derating



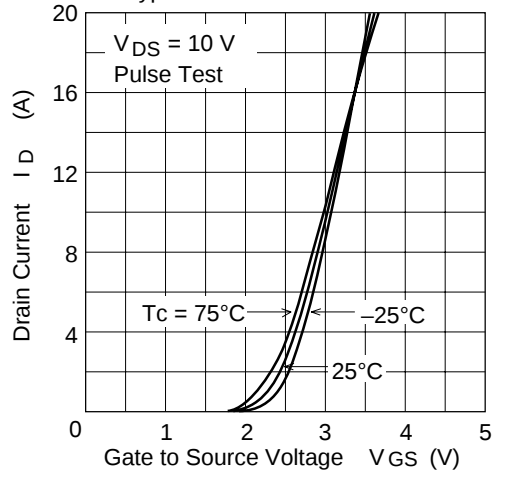
Maximum Safe Operation Area

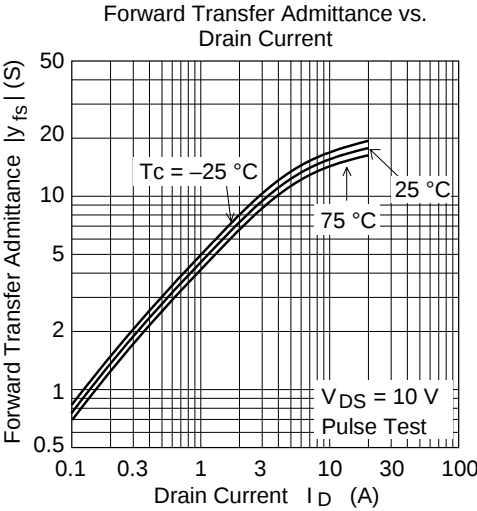
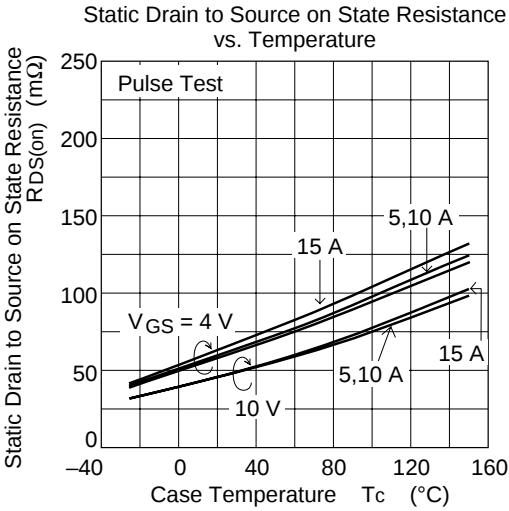
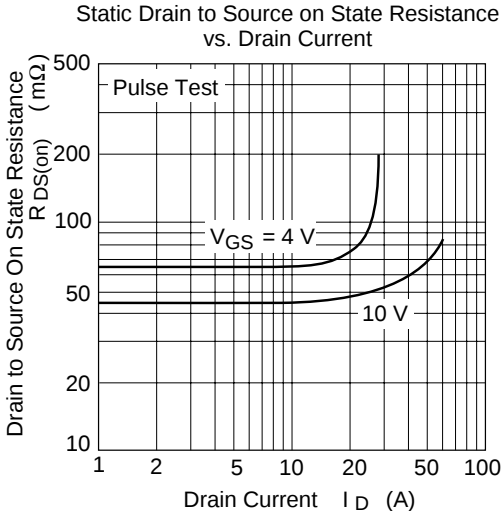
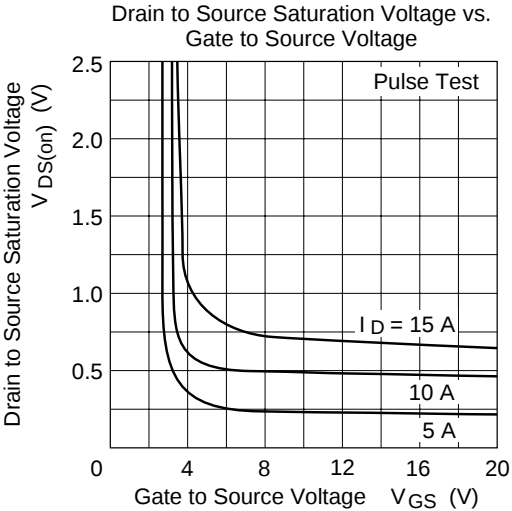


Typical Output Characteristics

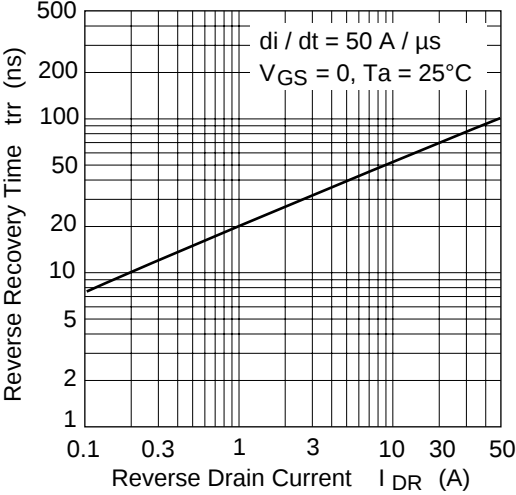


Typical Transfer Characteristics

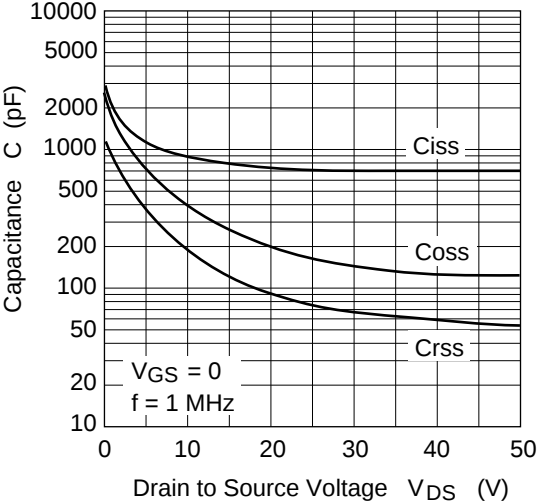




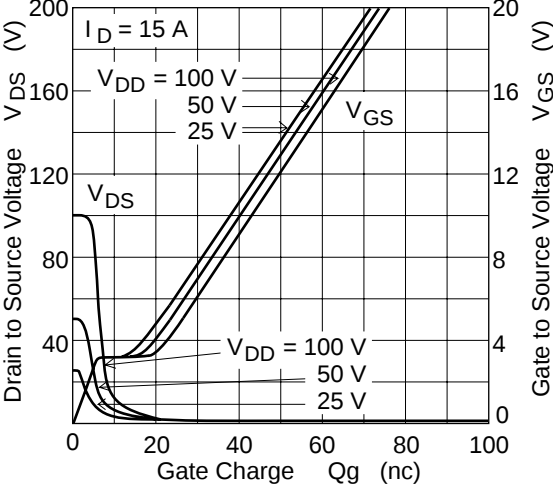
Body-Drain Diode Reverse Recovery Time



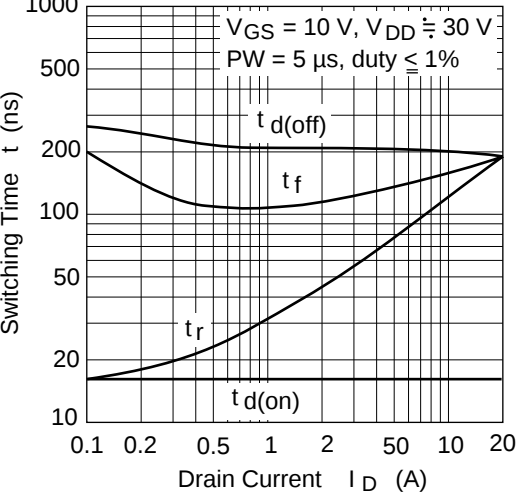
Typical Capacitance vs. Drain to Source Voltage

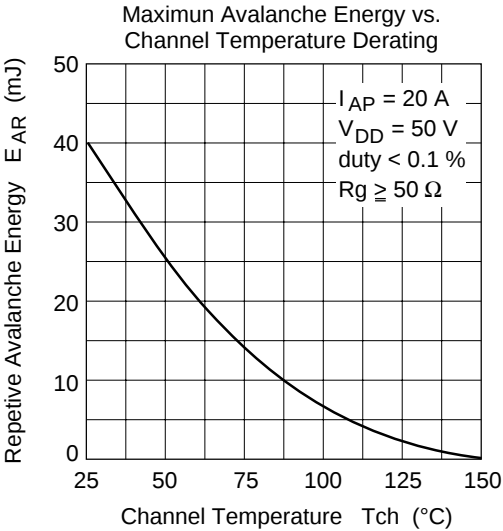
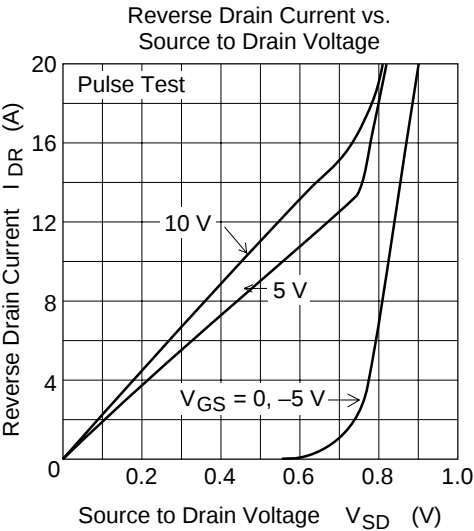


Dynamic Input Characteristics

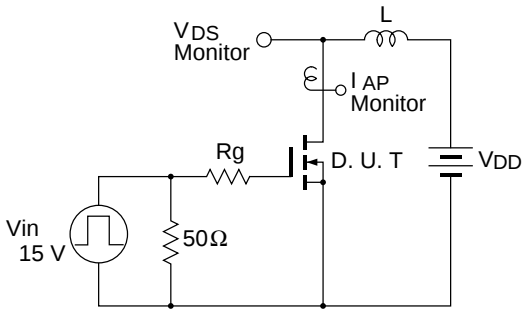


Switching Characteristics

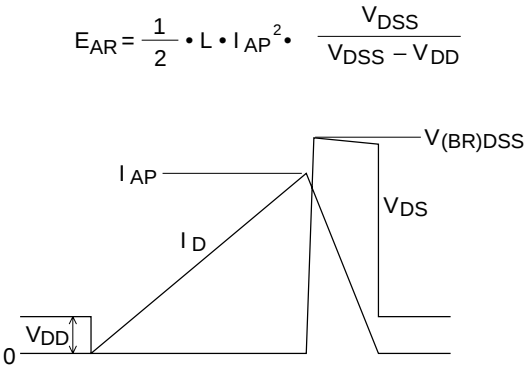




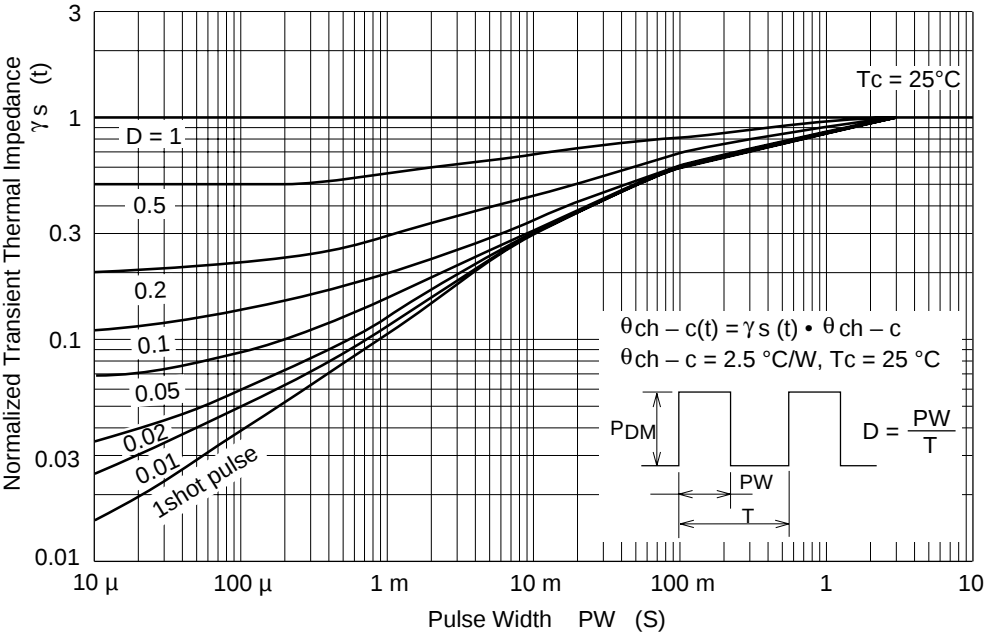
Avalanche Test Circuit



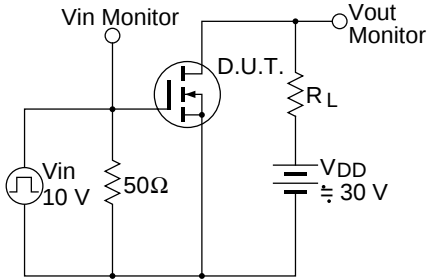
Avalanche Waveform



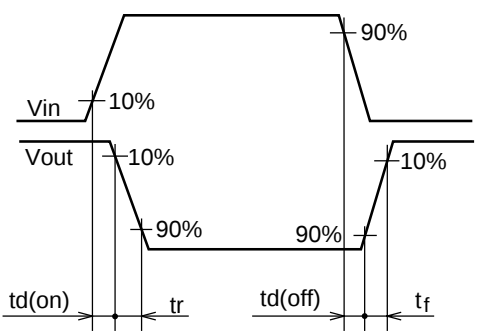
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit

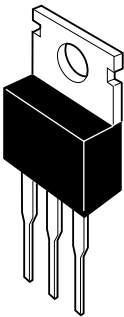
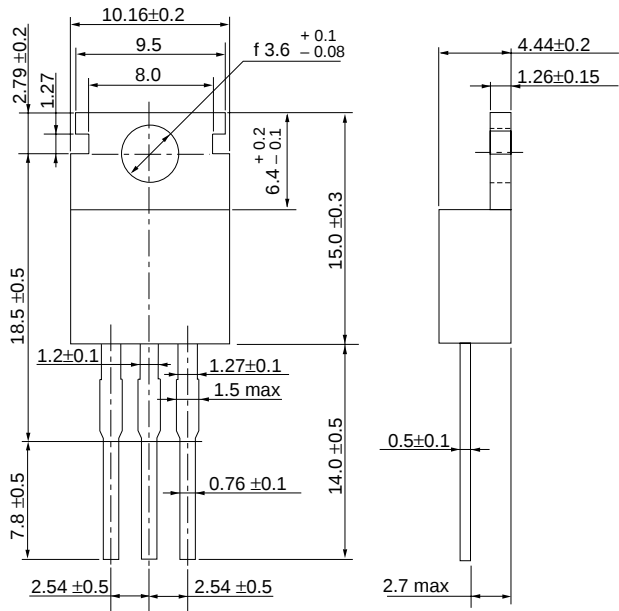


Waveform



Package Dimensions

Unit: mm



Hitachi Code	TO-220AB
EIAJ	SC-46
JEDEC	—

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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